

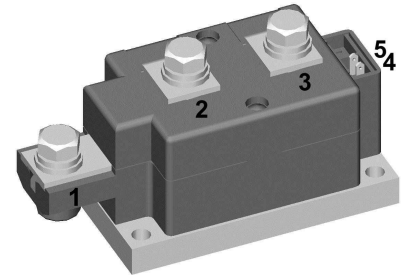
# Thyristor \ Diode Module

$V_{RRM} = 2 \times 1800 \text{ V}$   
 $I_{TAV} = 320 \text{ A}$   
 $V_T = 1.06 \text{ V}$

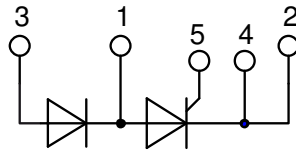
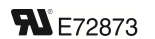
Phase leg

Part number

**MCD312-18io1**



Backside: isolated



### Features / Advantages:

- International standard package
- Direct copper bonded Al<sub>2</sub>O<sub>3</sub>-ceramic with copper base plate
- Planar passivated chip
- Isolation voltage 3600 V~
- Keyed gate/cathode twin pins

### Applications:

- Motor control, softstarter
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Solid state switches

### Package: Y1

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper internally DCB isolated
- Advanced power cycling

### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

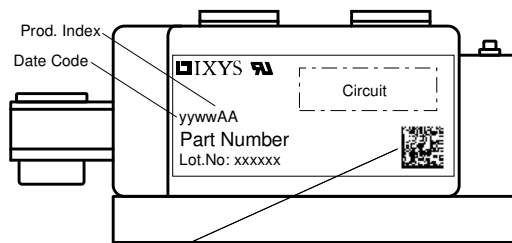
- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier			Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage				1900	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage				1800	V	
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1800\text{ V}$			1	mA	
		$V_{R/D} = 1800\text{ V}$			40	mA	
$V_T$	forward voltage drop	$I_T = 300\text{ A}$			1.12	V	
		$I_T = 600\text{ A}$			1.32	V	
		$I_T = 300\text{ A}$	$T_{VJ} = 125^\circ\text{C}$			1.06	V
		$I_T = 600\text{ A}$				1.29	V
$I_{TAV}$	average forward current	$T_C = 85^\circ\text{C}$			320	A	
$I_{T(RMS)}$	RMS forward current	180° sine			520	A	
$V_{T0}$	threshold voltage	} for power loss calculation only			0.80	V	
$r_T$	slope resistance				0.68	mΩ	
$R_{thJC}$	thermal resistance junction to case				0.12	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.040		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^\circ\text{C}$		960	W	
$I_{TSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		9.60	kA	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		10.4	kA	
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^\circ\text{C}$		8.16	kA	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		8.82	kA	
$I^2t$	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		460.8	kA <sup>2</sup> s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		447.4	kA <sup>2</sup> s	
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^\circ\text{C}$		332.9	kA <sup>2</sup> s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		323.3	kA <sup>2</sup> s	
$C_J$	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		438	pF	
$P_{GM}$	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 140^\circ\text{C}$		120	W	
		$t_p = 500\text{ }\mu\text{s}$			60	W	
$P_{GAV}$	average gate power dissipation				20	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^\circ\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 960\text{ A}$			100	A/ $\mu\text{s}$	
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 1\text{ A}/\mu\text{s};$ $I_G = 1\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 320\text{ A}$			500	A/ $\mu\text{s}$	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^\circ\text{C}$		1000	V/ $\mu\text{s}$	
		$R_{GK} = \infty$ ; method 1 (linear voltage rise)					
$V_{GT}$	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^\circ\text{C}$		2	V	
			$T_{VJ} = -40^\circ\text{C}$		3	V	
$I_{GT}$	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^\circ\text{C}$		150	mA	
			$T_{VJ} = -40^\circ\text{C}$		220	mA	
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^\circ\text{C}$		0.25	V	
$I_{GD}$	gate non-trigger current				10	mA	
$I_L$	latching current	$t_p = 30\text{ }\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$		200	mA	
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
$I_H$	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ\text{C}$		150	mA	
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^\circ\text{C}$		2	$\mu\text{s}$	
		$I_G = 1\text{ A}; di_G/dt = 1\text{ A}/\mu\text{s}$					
$t_q$	turn-off time	$V_R = 100\text{ V}; I_T = 300\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^\circ\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 50\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$		200		$\mu\text{s}$	

Package Y1				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			600	A
$T_{VJ}$	virtual junction temperature		-40		140	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				680		g
$M_D$	mounting torque		4.5		7	Nm
$M_T$	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	16.0			mm
$d_{Spb/Apb}$		terminal to backside	16.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



Data Matrix: Typ (1-19), DC+Prod.Index (20-25), FKT# (26-31)  
leer (33), lfd.# (33-36)

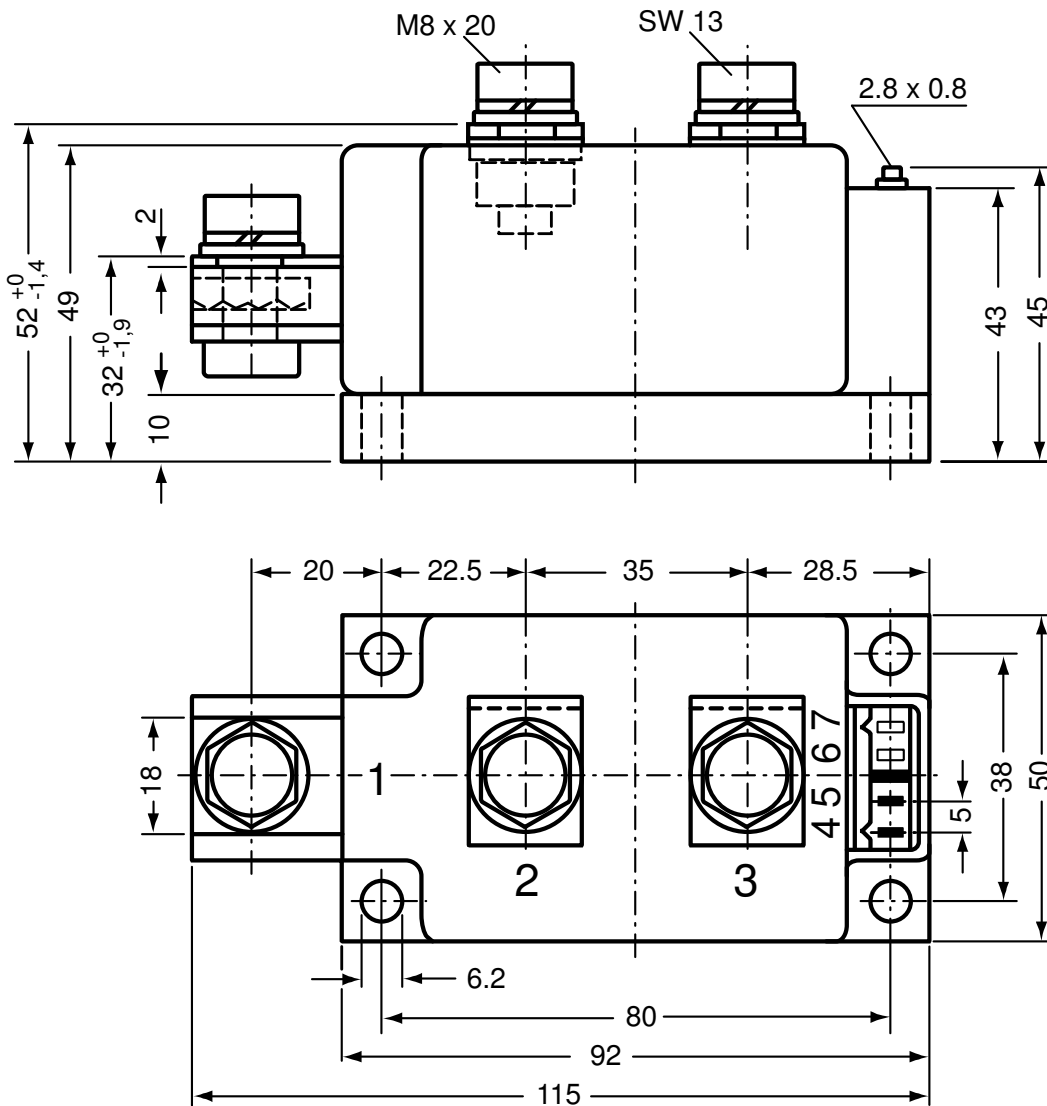
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD312-18io1	MCD312-18io1	Box	3	461865

**Equivalent Circuits for Simulation**
*\* on die level*
 $T_{VJ} = 140\text{ °C}$ 

**Thyristor**

$V_{0\ max}$	threshold voltage	0.8	V
$R_{0\ max}$	slope resistance *	0.5	mΩ

## Outlines Y1



### Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 180L (L = Left for pin pair 4/5)

Type ZY 180R (R = Right for pin pair 6/7) } UL 758, style 3751



**Thyristor**

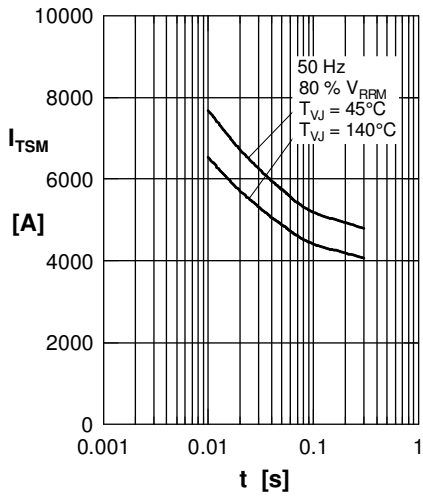


Fig. 1 Surge overload current  
 $I_{TSM}$ : Crest value,  $t$ : duration

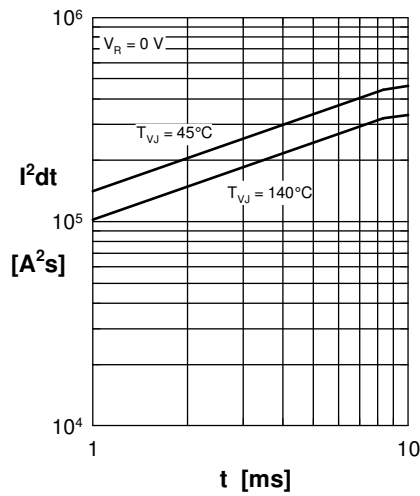


Fig. 2  $I^2dt$  versus time

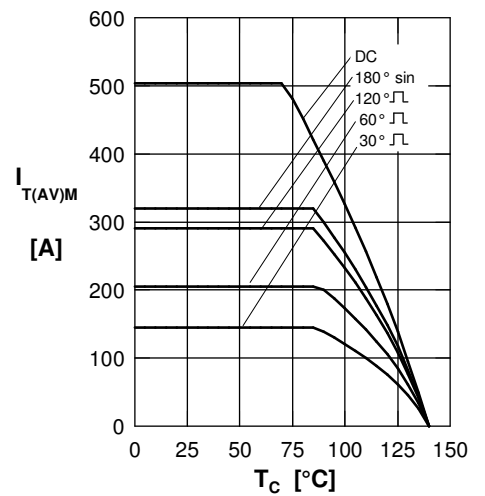


Fig. 3 Max. forward current at case temperature

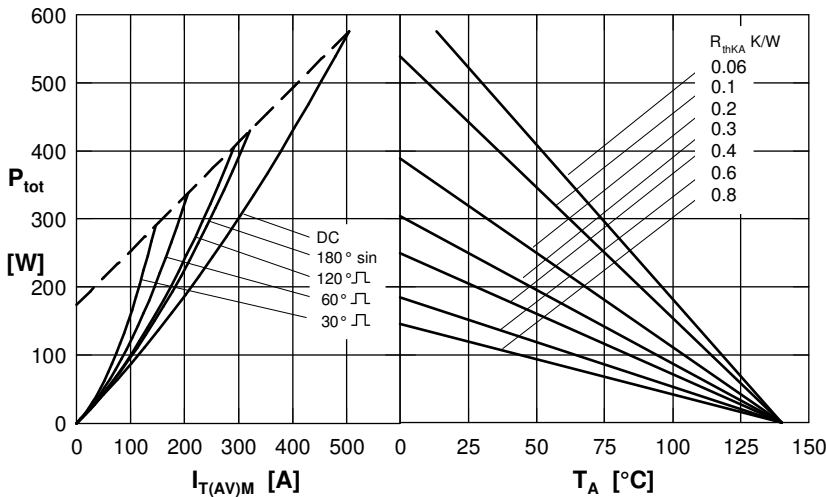


Fig. 4 Power dissipation versus on-state current and ambient temperature (per thyristor)

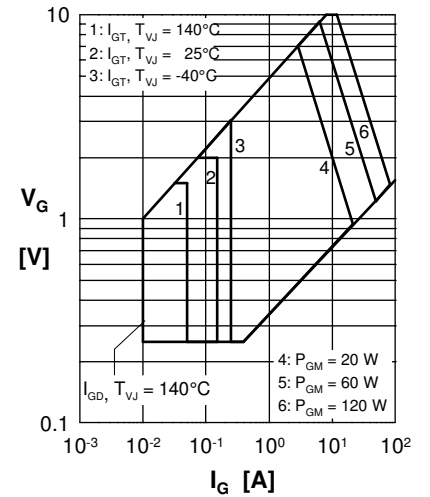


Fig. 5 Gate voltage & gate current

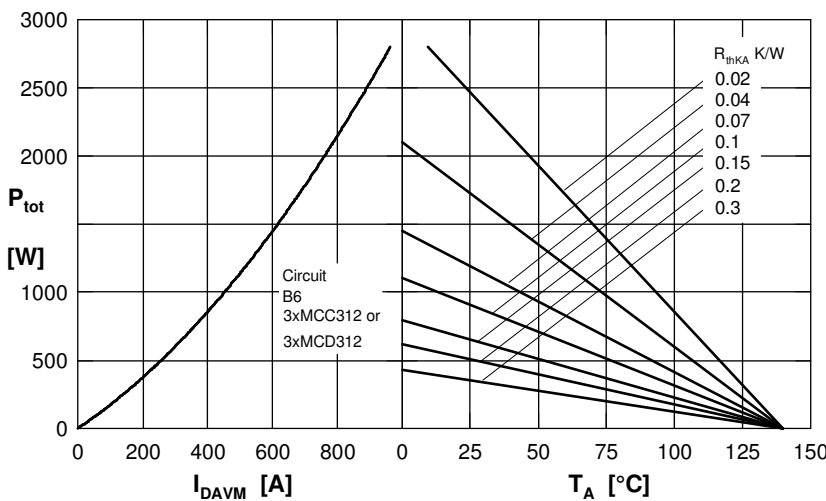


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

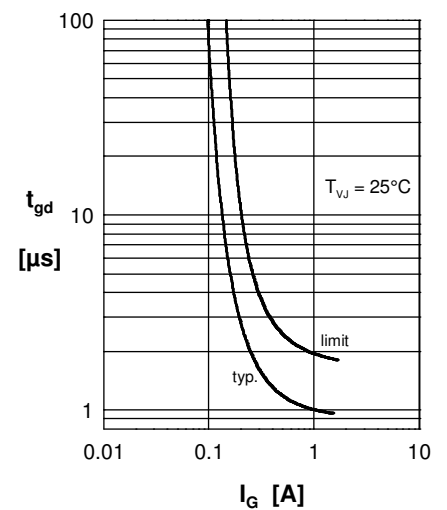


Fig. 7 Gate controlled delay time  $t_{gd}$

Rectifier

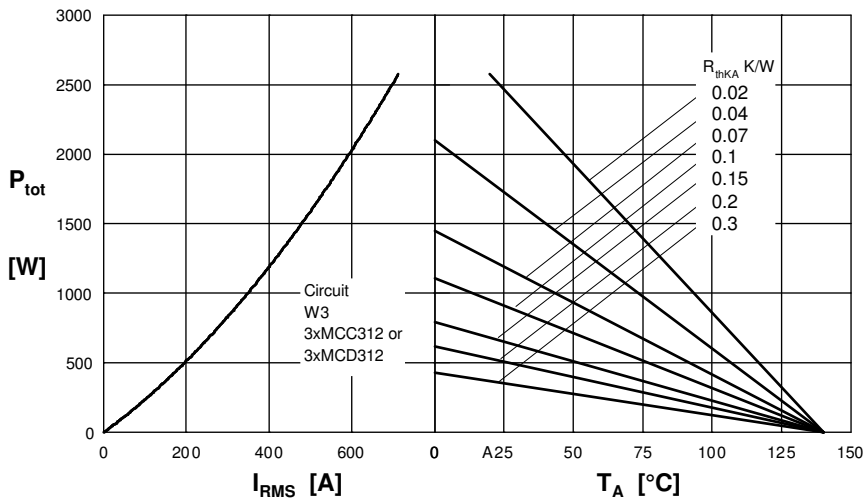


Fig. 8 Three phase AC-controller: Power dissipation versus  $R_{MS}$  output current and ambient temperature

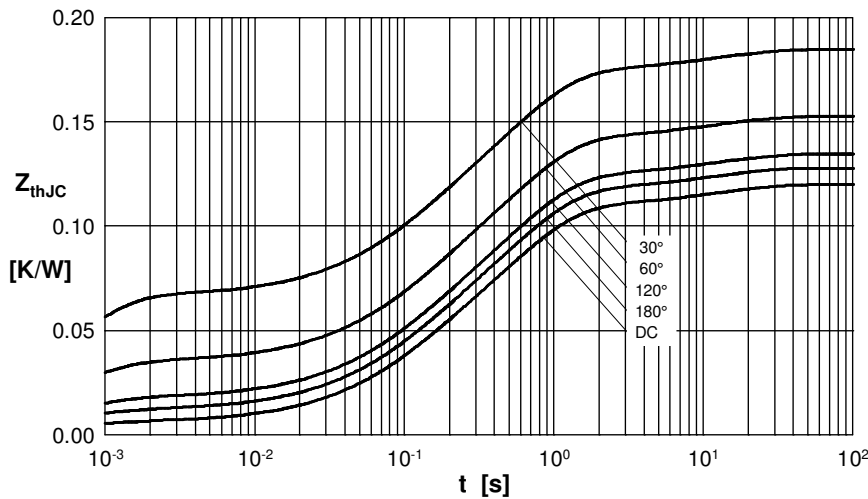


Fig. 9 Transient thermal impedance junction to case (per thyristor)

$R_{thJC}$  for various conduct. angles d:

d	$R_{thJC}$ [K/W]
DC	0.120
180°	0.128
120°	0.135
60°	0.153
30°	0.185

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0058	0.00054
2	0.0310	0.098
3	0.0720	0.54
4	0.0112	12

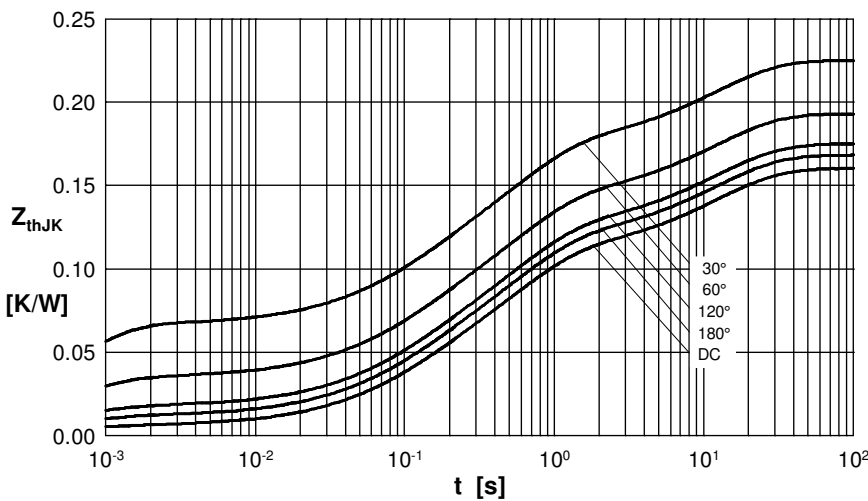


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor)

$R_{thJK}$  for various conduct. angles d:

d	$R_{thJK}$ [K/W]
DC	0.160
180°	0.168
120°	0.175
60°	0.193
30°	0.225

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0058	0.00054
2	0.0310	0.098
3	0.0720	0.54
4	0.0114	12
5	0.0400	12